

FORM PT01449
(REV. 8-83)U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICEATTY. DOCKET NO.
HARI.006USQSERIAL NO.
09/114504

INFORMATION DISCLOSURE STATEMENT

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U. S. PATENT DOCUMENTS

*EXAMINER INITIAL		DOCUMENT NUMBER							DATE	NAME	CLASS	SUB CLASS	FILING DATE
8 ^u	A1	3	8	9	5	3	6	0	7/75	Cricchi et al.			
	A2	3	8	9	8	6	3	2	8/75	Spencer, Jr.			
	A3	3	9	0	6	4	5	5	9/75	Houston et al.			
	A4	3	9	1	4	7	5	0	10/75	Hadden, Jr.			
	A5	4	0	4	4	3	3	9	8/77	Berg			
	A6	4	0	5	8	7	9	9	11/77	George et al.			
	A7	4	0	6	4	4	0	5	12/77	Cricchi et al.			
	A8	4	1	1	5	8	5	0	9/78	Houston et al.			
	A9	4	1	3	0	8	9	0	12/78	Adam			
	A10	4	1	4	1	0	8	1	2/79	Horne et al.			
8 ^u	A11	4	1	9	3	1	2	8	3/80	Brewer			

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		DOCUMENT NUMBER							DATE	COUNTRY	CLASS	SUB CLASS	TRANS.? (YES/NO)
8 ^u	B1	JP	58	0	8	6	7	7	5/1983	Japan			Abstract
	B2	JP	58	2	1	5	7	9	12/1983	Japan			Abstract
	B3	JP	58	2	1	5	7	9	5/1983	Japan			Yes
	B4	JP	59	1	6	2	6	9	9/1984	Japan			Abstract
8 ^u	B5	JP	62	2	8	3	4	9	12/1987	Japan			Abstract

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent pages, Etc.)

8 ^u	C1	Flash Memory Cards, Oct. 1992, pp. 4-91, 4-95, and 4-96.
8 ^u	C2	Cricchi et al., "Nonvolatile Block-Oriented RAM", IEEE International Solid-State Circuits Conference, Feb, 13-15, 1974, Digest of Technical Papers.
8 ^u	C3	Brewer et al., "Block-Oriented Random Access MNOS Memory", National Computer Conference and Exposition, Chicago, May 6-10, 1974, AFIPS Conference Proceedings, vol 43. Pp. 837-840.

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gu	A12 4 2 4 1 4 2 4	12/80	Dickson et al.			
	A13 4 4 1 2 3 0 9	10/83	Kuo			
	A14 4 4 2 8 0 4 7	1/84	Hayn et al.			
	A15 4 4 3 3 3 8 7	2/84	Dyer et al.			
	A16 4 5 2 7 2 5 7	7/85	Cricchi			
	A17 4 8 6 0 2 6 2	8/89	Chiu			
	A18 4 8 8 2 6 4 2	11/89	Tayler et al.			
	A19 4 8 8 7 2 3 4	12/89	Iijima			
	A20 4 9 2 0 4 7 8	4/90	Furuya et al.			
	A21 4 9 3 1 9 9 7	6/90	Mitsuishi et al.			
gu	A22 4 9 3 3 9 0 6	6/90	Terada et al.			

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	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB CLASS	TRANS.? (YES/NO)
gu	B6 JP 59 1 8 6 0 1 5	10/1984	Japan			Abstract
	B7 JP 62 2 8 3 4 9 6	12/1987	Japan			Yes
	B8 JP 63 1 8 3 7 0 0	7/1988	Japan			Abstract
	B9 JP 58 0 8 6 7 7 7	5/1983	Japan			Abstract
gu	B10 JP 52 0 0 8 7 3 8	1/1977	Japan			Abstract

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent pages, Etc.)

gu	C4	Brewer et al., Low Cost MNOS BORAM", Proceedings of IEEE National Aerospace Electronics Conference, NAECON '77, May 17-19, 1977.
gu	C5	Short, "Microprocessors and Programmed Logic", second edition. Ch 13.2.2 Electrically Erasable Programmable Read only Memory, EEPROM Prentice Hall International, 1987.
gu	C6	Fitzpatrick et al., "MNOS/SOS Memory Using High-Voltage Depletion-Mode CMOS Logic", Westinghouse Electric Corp., pp. 196-199.
	C7	SEEQ Technology Incorp., 48F512 512 Flash EEPROM, Preliminary Data Sheet, Oct 1988, pp. 2-1, 2-24.

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su	A23 4 9 4 9 3 0 9	8/90	Rao			
	A24 5 0 5 3 9 9 0	10/91	Kreifels et al.			
	A26 5 0 8 4 8 4 3	1/92	Mitsubishi et al.			
	A27 5 2 2 4 0 7 0	6/93	Fandrich et al.			
	A28 5 2 6 7 2 1 8	11/93	Elbert			
	A29 5 3 0 1 1 6 1	4/94	Landgraf et al.			
	A30 5 3 4 1 3 3 0	8/94	Wells et al.			
	A31 5 3 6 3 3 3 4	11/94	Alexander et al.			
	A32 5 4 1 8 7 5 2	5/95	Harari et al.			
	A33 5 6 4 8 9 2 9	7/97	Miyamoto			
su	A34 5 7 1 9 8 0 8	2/98	Harari et al.			

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	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB CLASS	TRANS.? (YES/NO)
su	B11 EP 0 2 8 3 2 3 8	9/1988	EPO			
su	B12 JP 63 1 0 6 9 8 9	5/1988	Japan			Abstract
su	B13 JP 63 2 2 5 9 9 9	9/1988	Japan			Abstract

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent pages, Etc.)

su	C8	Intel Corporation, 27F256 256K (32K x 8) CMOS Flash Memory", Data Sheet, May 1988, pp. 1-21.
su	C9	Cricchi et al., "The Drain-Source Protected MNOS Memory Device and Memory Endurance", IEDM Technical Digest, 1973, pp. 126-129.
su	C10	Cormier, "Erasable/Programmable Solid-State Memories", EDN, pp. 145-154, November 14, 1985, pp. 145-154.

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